

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1265	Semiconductor? and topology	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:00
L2	110	1 and (aspect near2 ratio)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:01
L3	3	2 and (electron near2 microscope)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:01
L4	5	2 and (contact near2 hole?)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:01
L5	203	1 and (inspect near4 hole or defect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:02
L6	14	5 and (electron near2 microscope)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:03
L7	4326	((250/310,492.2;) or (382/145, 149;)).CCLS	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/04 12:04
L8	3	7 and (inspect near2 semiconductor?)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:05

10/614,825

L9	193	7 and (aspect near2 ratio)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:05
L10	65	9 and (inspect near4 semiconductor or defect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:06
L11	25	10 and (contact near2 hole)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:06
L12	19	11 and (electron near2 microscope)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:07
L13	9	"6,373,054"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:07

1/4/05

Sample 1

"Method for the Electron-microscopic observation of Semiconductor Arrangement and Apparatus Therefor" by Kleuzle et al

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L7	4326	((250/310,492.2,) or (382/145, 149,)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/04 12:04
L8	3	7 and (inspect near2 semiconductor?)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:05

10/6/4, 825

L9	193	7 and (aspect near2 ratio)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:05
L10	65	9 and (inspect near4 semiconductor or defect)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:06
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L13	9	"6,373,054"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/01/04 12:07

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